This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claim 1 (previously presented): A method for adjusting a frequency characteristic of an edge reflection type surface acoustic wave device, comprising the steps of:

determining the frequency characteristic of a first edge reflection type surface acoustic wave device having a piezoelectric substrate that is a first edge reflection type surface acoustic wave device cut from a piezoelectric wafer, the first edge reflection type surface acoustic wave device having a pair of edges of the piezoelectric substrate which define a predetermined distance therebetween; and

cutting the piezoelectric wafer for additional edge reflection type surface acoustic wave devices, which are subsequently cut from the piezoelectric wafer after the first edge reflection type surface acoustic wave device is cut, at at least one of a pair of positions which define a distance that is shorter than the predetermined distance when a final frequency characteristic of the additional edge reflection type surface acoustic wave devices is to be higher than an obtained frequency characteristic of the first edge reflection type surface acoustic wave device, and cutting the piezoelectric wafer at at least one of a pair of positions which define a distance that is longer than the predetermined distance when a final frequency characteristic of the additional edge reflection type surface acoustic wave devices is to be lower than the obtained frequency characteristic.

Claim 2 (previously presented): A method for adjusting a frequency characteristic of an edge reflection type surface acoustic wave device according to claim 1, wherein the positions at which the piezoelectric wafer is cut in the cutting step is shifted from positions of the edges which define the predetermined distance in the frequency

characteristic obtaining step by about $\lambda/8$ or less, where the λ is wavelength of a shear horizontal type surface wave to be excited in the additional edge reflection type surface acoustic wave devices.

Claim 3 (previously presented): A method for adjusting a frequency characteristic of an edge reflection type surface acoustic wave device according to claim 1, wherein the positions at which the piezoelectric wafer is cut in the cutting step is shifted from positions of the edges which define the predetermined distance in the frequency characteristic obtaining step by about $\lambda/16$ or less, where the λ is wavelength of a shear horizontal type surface wave to be excited in the additional edge reflection type surface acoustic wave devices.

Claim 4 (previously presented): A method for adjusting a frequency characteristic of an edge reflection type surface acoustic wave device according to claim 1, wherein each of the first and additional edge reflection type surface acoustic wave devices comprise a single electrode type interdigital transducer.

Claim 5 (original): A method for adjusting a frequency characteristic of an edge reflection type surface acoustic wave device according to claim 4, wherein the positions of the edges which define the predetermined distance are located at approximate centers of electrodes.

Claim 6 (previously presented): A method for adjusting a frequency characteristic of an edge reflection type surface acoustic wave device according to claim 1, wherein each of the first and additional edge reflection type surface acoustic wave devices comprise a double electrode type interdigital transducer.

Claim 7 (previously presented); A method for adjusting a frequency characteristic of an edge reflection type surface acoustic wave device according to claim 6, wherein each of the positions of the edges which define the predetermined distance is located at an approximate center of a pair of electrode fingers constituting the double electrode.

Claims 8-15 (canceled).